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**DECLARATION OF SOLE INVENTOR FOR PATENT APPLICATION**

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: Methods of Forming Silicon Nitride, Methods of Forming Transistor Devices, and Transistor Devices, the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations §1.56.

**PRIOR FOREIGN APPLICATIONS:**

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so

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1 made are punishable by fine or imprisonment, or both, under  
2 Section 1001 of Title 18 of the United States Code and that such willful  
3 false statement may jeopardize the validity of the application or any  
4 patent issued therefrom.

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6 \* \* \* \* \*

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8 Full name of sole inventor: John T. Moore

9 Inventor's Signature: 

10 Date: 6/14/00

11 Residence: Boise, ID

12 Citizenship: US

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